

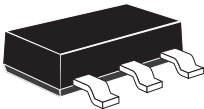
ZXMN10A11G

100V N-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY  
 $V_{(BR)DSS}= 100V$ ;  $R_{DS(ON)}= 0.6\Omega$   $I_D= 1.8A$

DESCRIPTION

This new generation of TRENCH MOSFETs from Zetex utilises a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



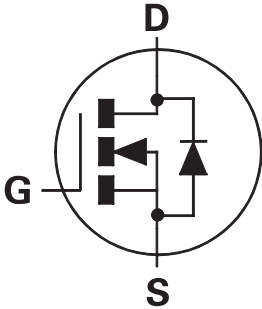
SOT223

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT223 package

APPLICATIONS

- DC - DC Converters
- Power Management Functions
- Relay and Solenoid driving
- Motor control

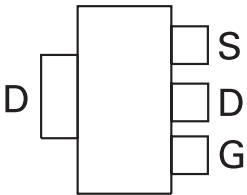


ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMN10A11GFTA	7"	12mm	1000 units
ZXMN10A11GFTC	13"	12mm	4000 units

DEVICE MARKING

- ZXMN  
10A11



Top View

# ZXMN10A11G

## ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DSS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current $V_{GS}=10V$ ; $T_A=25^{\circ}C$ (b) $V_{GS}=10V$ ; $T_A=70^{\circ}C$ (b) $V_{GS}=10V$ ; $T_A=25^{\circ}C$ (a)	$I_D$	1.8 1.4 1.3	A
Pulsed Drain Current (c)	$I_{DM}$	5.8	A
Continuous Source Current (Body Diode) (b)	$I_S$	4.6	A
Pulsed Source Current (Body Diode)(c)	$I_{SM}$	5.8	A
Power Dissipation at $T_A=25^{\circ}C$ (a) Linear Derating Factor	$P_D$	2 16	W mW/ $^{\circ}C$
Power Dissipation at $T_A=25^{\circ}C$ (b) Linear Derating Factor	$P_D$	3.9 31	W mW/ $^{\circ}C$
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^{\circ}C$

## THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	62.5	$^{\circ}C/W$
Junction to Ambient (b)	$R_{\theta JA}$	32	$^{\circ}C/W$

### NOTES

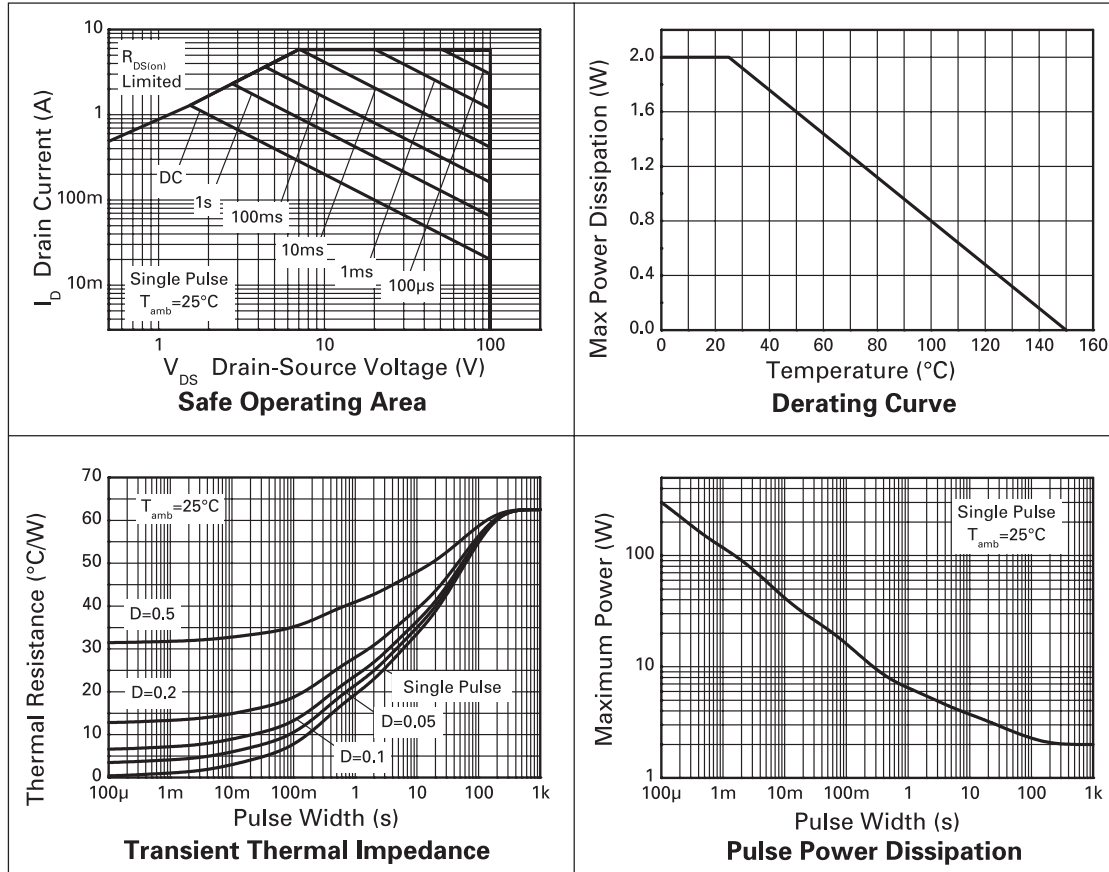
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at  $t \leq 10$  secs.

(c) Repetitive rating 25mm x 25mm FRA PCB,  $D=0.05$  pulse width = 10 $\mu s$  - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

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## CHARACTERISTICS



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## ELECTRICAL CHARACTERISTICS (at TA = 25°C unless otherwise stated)

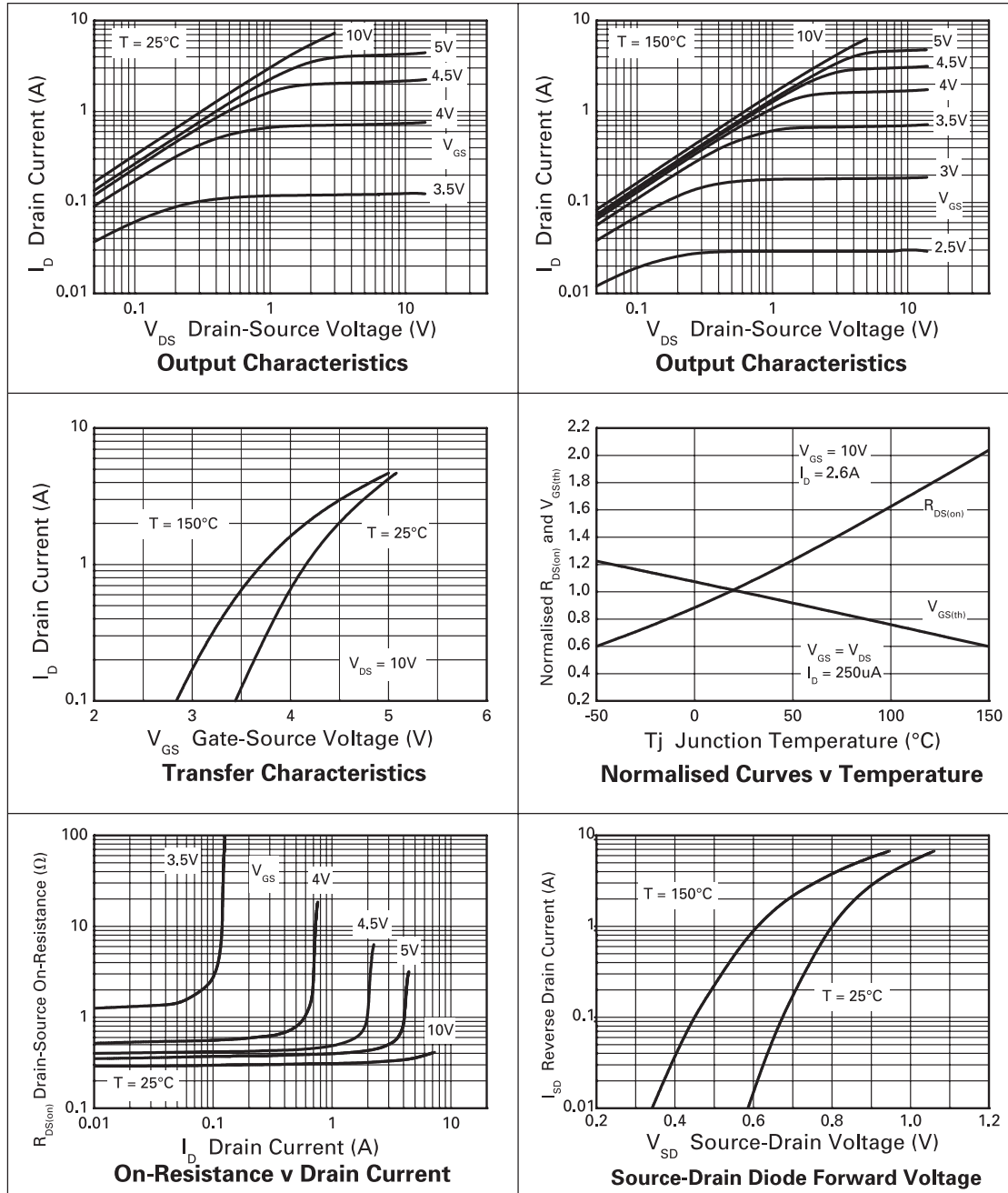
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	V(BR)DSS	100			V	ID=250μA, VGS=0V
Zero Gate Voltage Drain Current	IDSS			1	μA	VDS=100V, VGS=0V
Gate-Body Leakage	IGSS			100	nA	VGS=±20V, VDS=0V
Gate-Source Threshold Voltage	VGS(th)	2.0		4.0	V	ID=250μA, VDS= VGS
Static Drain-Source On-State Resistance (1)	RDS(on)			0.60 0.70	Ω Ω	VGS=10V, ID=2.6A VGS=6V, ID=1.3A
Forward Transconductance (3)	gfs		3.95		S	VDS=15V,ID=2.6A
DYNAMIC (3)						
Input Capacitance	Ciss		274		pF	VDS=50 V, VGS=0V, f=1MHz
Output Capacitance	Coss		21		pF	
Reverse Transfer Capacitance	Crss		11		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	td(on)		2.7		ns	VDD =50V, ID=1A RG=6.0Ω, VGS=10V
Rise Time	tr		1.7		ns	
Turn-Off Delay Time	td(off)		7.4		ns	
Fall Time	tf		3.5		ns	
Gate Charge	Qg		3		nC	VDS=50V, VGS=5V, ID=2.5A
Total Gate Charge	Qg		5.4		nC	VDS=50V,VGS=10V, ID=2.5A
Gate-Source Charge	Qgs		1.4		nC	
Gate-Drain Charge	Qgd		1.5		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	VSD		0.85	0.95	V	TJ=25°C, IS=1.85A, VGS=0V
Reverse Recovery Time (3)	trr		26		ns	TJ=25°C, IF=1.0A, di/dt= 100A/μs
Reverse Recovery Charge (3)	Qrr		30		nC	

### NOTES

- (1) Measured under pulsed conditions. Width $\leq 300\mu s$ . Duty cycle  $\leq 2\%$ .  
 (2) Switching characteristics are independent of operating junction temperature.  
 (3) For design aid only, not subject to production testing.

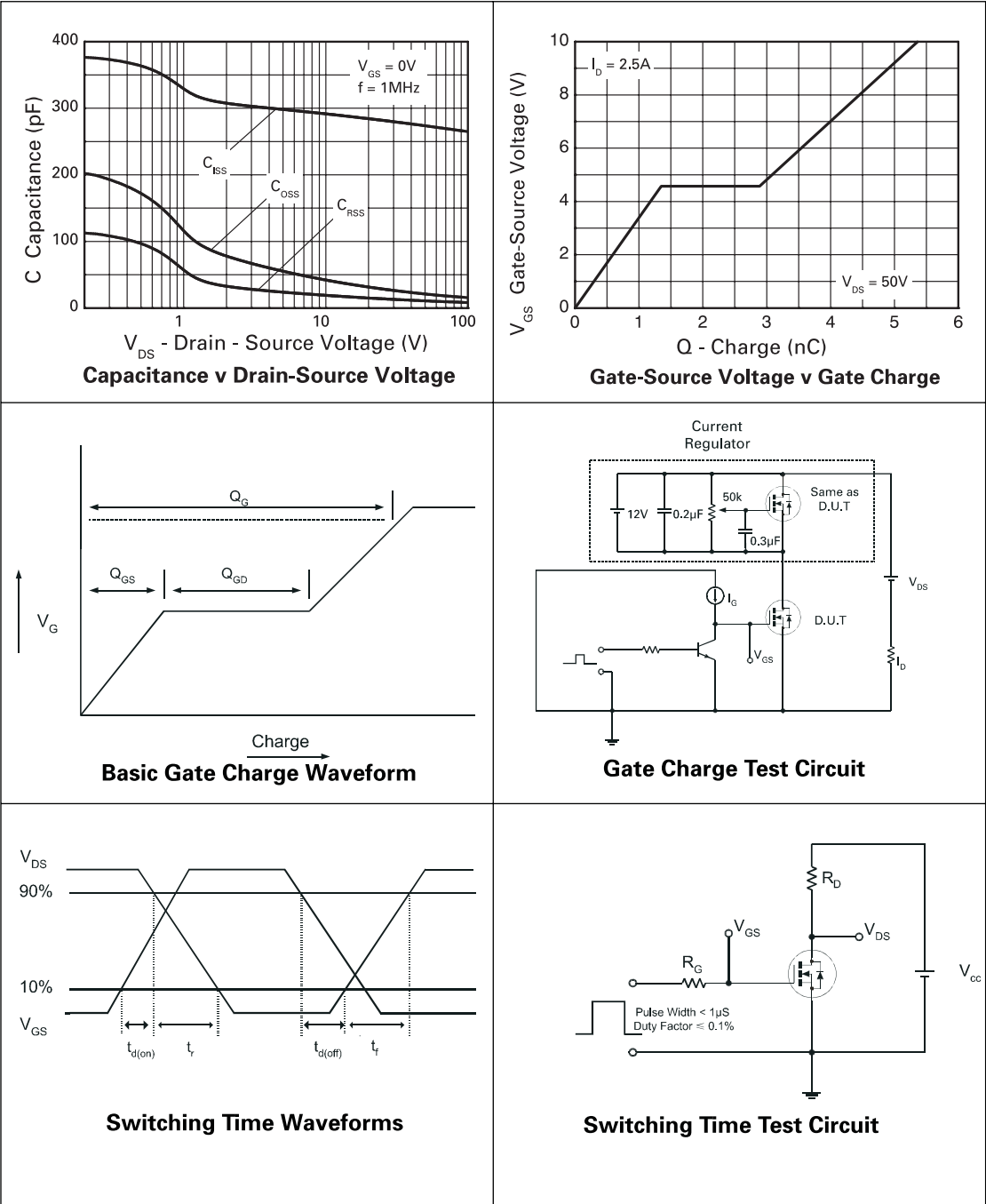
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## TYPICAL CHARACTERISTICS



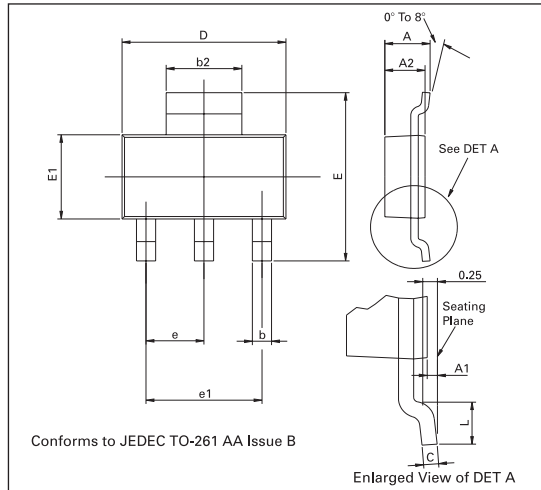
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## TYPICAL CHARACTERISTICS



# ZXMN10A11G

## PACKAGE OUTLINE



## PACKAGE DIMENSIONS

DIM	MILLIMETRES	
	MIN	MAX
A	—	1.80
A1	0.02	0.10
A2	1.55	1.65
b	0.66	0.84
b2	2.90	3.10
C	0.23	0.33
D	6.30	6.70
e	2.30 BASIC	
e1	4.60 BASIC	
E	6.70	7.30
E1	3.30	3.70
L	0.90	—

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ISSUE 1 - MARCH 2002

ZETEX